

M6MGB/T64BS4AWG

**67,108,864-BIT (4,194,304-WORD BY 16-BIT) CMOS FLASH MEMORY &
4,194,304-BIT (262,144-WORD BY 16-BIT) CMOS SRAM**
Stacked-CSP (Chip Scale Package)

Description

The M6MGB/T64BS4AWG is a Stacked Chip Scale Package (S-CSP) that contains 64M-bit Flash memory and 4M-bit SRAM in a 67-pin Stacked CSP for lead free use.

64M-bit Flash memory is a 4,194,304 words, single power supply and high performance non-volatile memory fabricated by CMOS technology for the peripheral circuit and DINOR IV (Divided bit-line NOR IV) architecture for the memory cell. All memory blocks are locked and can not be programmed or erased, when F-WP# is Low. Using Software Lock Release function, program or erase operation can be executed.

4M-bit SRAM is a 262,144 words asynchronous SRAM fabricated by CMOS technology for the peripheral circuit and TFT type transistor for the memory cell.

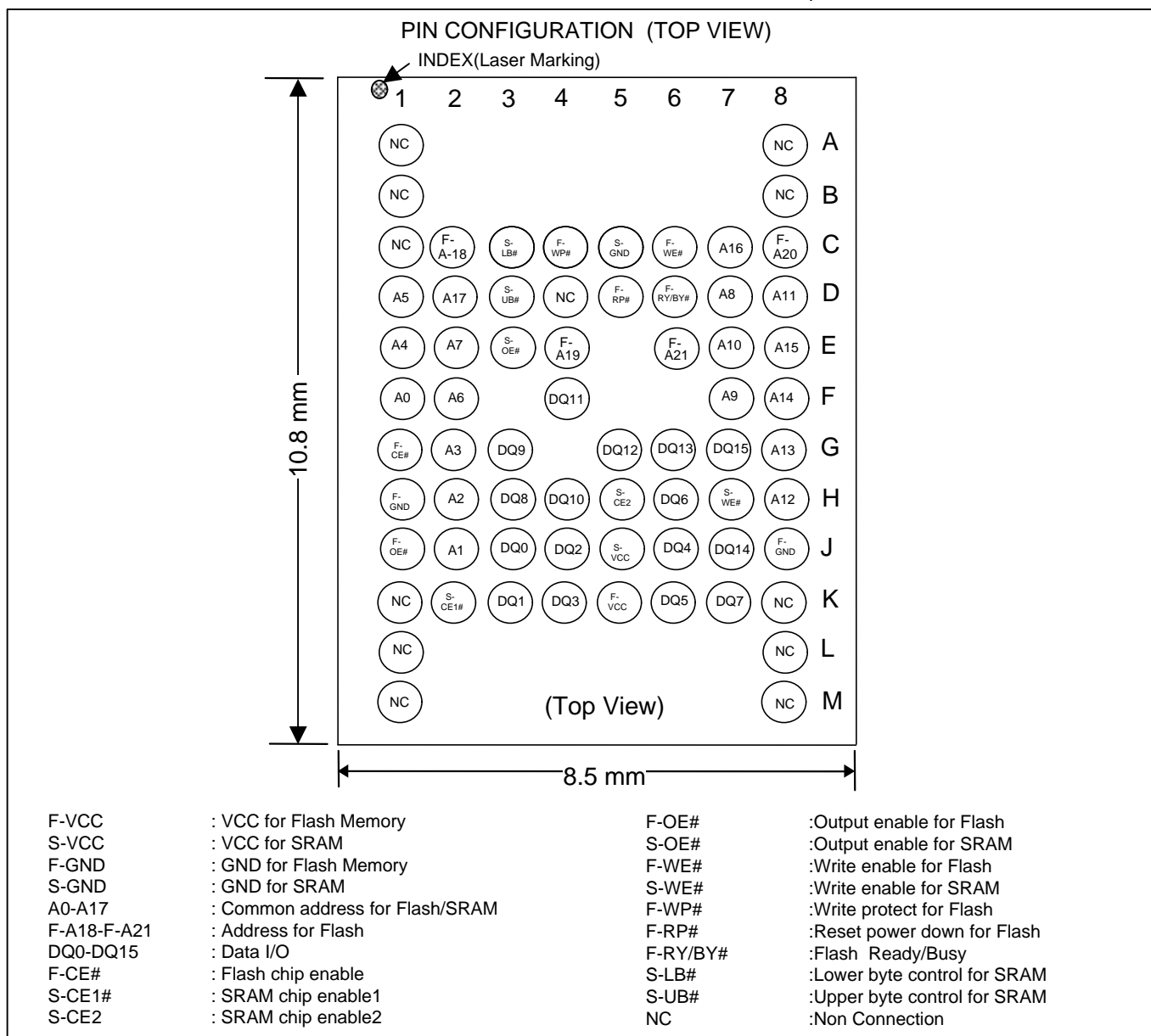
The M6MGB/T64BS4AWG is suitable for a high performance cellular phone and a mobile PC that are required to be small mounting area, weight and small power dissipation.

Features

Access Time	Flash	70ns (Max.)
	SRAM	85ns (Max.)
Supply Voltage		F-VCC =S-VCC=2.7 ~ 3.0V
Ambient Temperature		Ta= -40 ~ 85 degree
Package		67pin S-CSP, Ball pitch 0.80mm Outer-ball:Su-Ag-Cu

Application

Mobile communication products

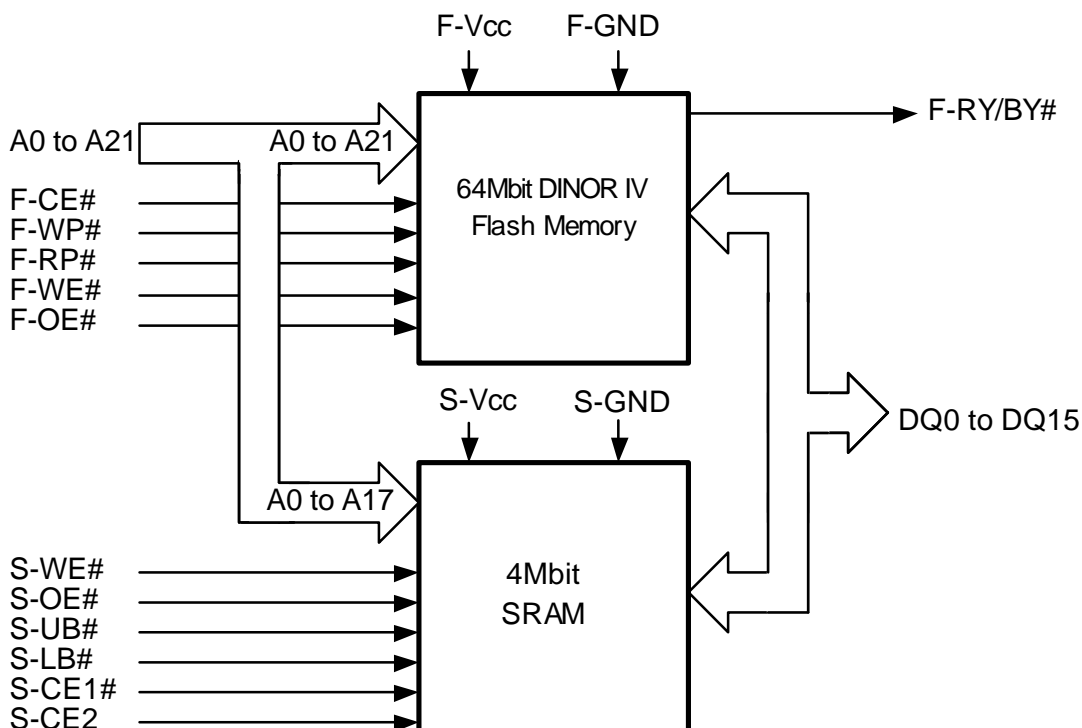


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MCP Block Diagram



Note: In the Flash memory part there are "Vcc", "GND", "OE#" and "WE#" which mean "F-Vcc", "F-GND", "F-OE#" and "F-WE#", respectively. In the SRAM part there are "GND", "UB#", "LB#", "OE#" and "WE#" which mean "S-GND", "S-UB#", "S-LB#", "S-OE#" and "S-WE#", respectively.

Capacitance

Symbol	Parameter		Conditions	Limits			Unit
				Min.	Typ.	Max.	
CIN	Input capacitance	A21-A0, F-OE#, F-WE#, F-CE#, F-WP#, F-RP#, S-CE1#, S-CE2, S-OE#, S-WE#, S-LB#, S-UB#	Ta=25°C, f=1MHz, Vin=Vout=0V			18	pF
COUT	Output Capacitance	DQ15-DQ0, F-RY/BY#				22	pF

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